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DATA SHEET

RENESAS

mos INTEGRATED CIRCUIT hase-out/Discontinued $\mu PD78P356$

16 BIT SINGLE-CHIP MICROCOMPUTER

The μ PD78P356 is produced by replacing the internal mask ROM of the μ PD78356 with a one-time PROM or EPROM. One-time PROM products, in which data can be written once are effective for manufacture of small quantities of multiple products and early stage start-up of application. EPROM products, to which programs can be re-written after previously written programs have been erased, are suited for system evaluation.

The following user's manuals completely describe the functions of the μ PD78P356. Be sure to read them before designing an application system.

μ PD78356	User's Manual, Hardware	: IEU-1361
μ ΡD7835 6	User's Manual, Instruction	: IEU-1395

FEATURES

- Compatible with the μPD78356
 - Can be replaced with the μ PD78356 containing mask ROM on a full-production basis.
- Internal PROM: 48K bytes
 - · Data can be written once (one-time PROM product without an erasure window)
 - Written data can be erased by exposure to ultraviolet light and re-written electrically (EPROM product with an erasure window)
- Contained ECC circuit
 - The circuit ensures that highly reliable data is stored in the internal PROM.
- PROM programming: Same as for the μPD27C1001A
- QTOPTM microcomputer
 - **Remark** The QTOP microcomputer is a single-chip microcomputer with a built-in one-time PROM that is totally supported by NEC. The support includes writing application programs, marking, screening, and verification.

ORDERING INFORMATION

Part number	Package	Internal ROM
μPD78P356GC-7EA	100-pin plastic QFP (14 × 14 mm)	One-time PROM
μPD78P356GD-5BB	120-pin plastic QFP (28 \times 28 mm)	One-time PROM
μPD78P356KP-S Note	120-pin ceramic WQFN	EPROM

Note Under development

In this manual, the description of the PROM is for both a one-time PROM and EPROM.

The information in this document is subject to change without notice.

Phase-out/Discontinued

PIN CONFIGURATION (TOP VIEW)

- (1) Normal operation mode (MODE0 = L, MODE1 = L)
 - **100-pin plastic QFP (14** × 14 mm) μPD78P356GC-7EA





Remark Pin compatible with the μ PD78356GC



- **120-pin plastic QFP (28 × 28 mm)** μPD78P356GD-5BB
- **120-pin ceramic WQFN** μPD78P356KP-S



Caution Connect the MODE0 and MODE1 pins directly to the Vss pins.

Remark Pin compatible with the μ PD78356GD

Phase-out/Discontinued

			—		
P00-P07	:	Port 0	SI00, SI10	:]	Serial input
P10-P17	:	Port 1	SI11	:}	Senai input
P20-P27	:	Port 2	SO00, SO10	: ר	Carial autout
P30-P37	:	Port 3	SO11	:}	Serial output
P40-P47	:	Port 4	SB0, SB1	:	Serial bus
P50-P57	:	Port 5	SCK00, SCK10	:	Serial clock
P70-P77	:	Port 7	SCK11	:∫	Serial Clock
P80-P87	:	Port 8	PWM0, PWM1	:	Pulse width modulation output
P90-P93	:	Port 9	WDTO	:	Watchdog timer output
P100-P107	:	Port 10	MODE0, MODE1	:	Mode
RTP0-RTP7	:	Real-time port	AD0-AD15	:	Address/data bus
NMI	:	Nonmaskable interrupt	ASTB	:	Address strobe
INTP0-INTP4	:	Interrupt from peripherals	RD	:	Read strobe
TO00-TO05	:]		LWR	:	Low-address write strobe
TO10, TO11	: }	Timer output	HWR	:	High-address write strobe
TO20, TO21	:J		WAIT	:	Wait
TCLR0-TCLR2	:	Timer clear input	CLKOUT	:	Clock output
TCLRUD	:∫	Timer clear mput	RESET	:	Reset
TIO, TI1	:	Timer input	X1,X2	:	Crystal
TIUD	:	Count pulse input	AVDD	:	Analog VDD
TCUD	:	Control pulse input	AVss	:	Analog Vss
ANIO-ANI7	:	Analog input	AVREF1-AVREF3	:	Analog reference voltage
ADTRG0-ADTRG3	3:	A/D trigger input	VDD	:	Power supply
ANO0, ANO1	:	Analog output	Vss	:	Ground
TxD	:	Transmit data	NC	:	No connection
RxD	:	Receive data			

(2) PROM programming mode (MODE0/VPP = +5 V, MODE1 = G, P21 = G, RESET = G)

Phase-out/Discontinued

 100-pin plastic QFP (14 × 14 mm) μPD78P356GC-7EA

NEC



- Caution Symbols in parentheses denote how the pins not used in the PROM programming mode should be treated.
 - L : Connect these pins to the Vss pins through separate resistors.
 - G : Connect these pins to the Vss pins.
 - Open: Do not connect these pins to anything.

- 120-pin plastic QFP (28 × 28 mm) μPD78P356GD-5BB
- **120-pin ceramic WQFN** μPD78P356KP-S



Phase-out/Discontinued

Caution Symbols in parentheses denote how the pins not used in the PROM programming mode should be treated.

- L : Connect these pins to the Vss pins through separate resistors.
- G : Connect these pins to the Vss pins.

Open: Do not connect these pins to anything.

A0-A16	: Address bus	MODE0, MODE1	ן : ו	
D0-D7	: Data bus	P21	: }	Programming mode set
CE	: Chip enable	RESET	:	
ŌĒ	: Output enable	VDD	:	Power supply
PGM	: Programming mode	Vss	:	Ground
		Vpp	:	Programming power supply

BLOCK DIAGRAM

NEC



Note Pins used in the PROM programming mode

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1. PIN FUNCTIONS

1.1 NORMAL OPERATION MODE (MODE0 = L, MODE1 = L)

(1) Port pins (1/2)

Pin	I/O	Function	Dual-function pin
P00	I/O	Port 0.	RTP0/ADTRG0
P01		8-bit I/O port.	RTP1/ADTRG1
P02]	Can be specified as input or output bit by bit.	RTP2/ADTRG2
P03			RTP3/ADTRG3
P04-P07			RTP4-RTP7
P10-P17	I/O	Port 1. 8-bit I/O port. Can be specified as input or output bit by bit.	-
P20	I	Port 2.	NMI
P21	1/0	8-bit I/O port. Can be specified as input or output bit by bit.	INTP0/TO04
P22		(P20/NMI is excluded.)	INTP1/TO05
P23			INTP2
P24			INTP3
P25			INTP4
P26			TCLR2/TO21
P27			ТО20
P30	1/0	Port 3.	TxD
P31		8-bit I/O port. Can be specified as input or output bit by bit.	RxD
P32	-	Can be specified as input of output bit by bit.	SO00/SB0
P33			SI00/SB1
P34			SCK00
P35			TCLR1
P36			TI1/TO11
P37	-		TO10
P40-P47	I/O	Port 4. 8-bit I/O port. Can be specified as input or output in units of 8 bits.	AD0-AD7
P50-P57	I/O	Port 5. 8-bit I/O port. Can be specified as input or output bit by bit.	AD8-AD15
P70-P77	I	Port 7. Port used only for 8-bit input.	ANIO-ANI7



(1) Port pins (2/2)

Pin	I/O	Function	Dual-function pin
P80	I/O	Port 8.	TCLR0
P81	7	8-bit I/O port.	T10/TO03
P82		Can be specified as input or output bit by bit.	TO00
P83	-		TO01
P84			TO02
P85			TCLRUD
.P86			PWM0
P87			PWM1
P90	I/O	Port 9.	RD
P91		4-bit I/O port.	LWR
P92		Can be specified as input or output bit by bit.	HWR
P93			-
P100	I/O	Port 10.	SO10
P101		8-bit I/O port.	SI10
P102		Can be specified as input or output bit by bit.	SCK10
P103			SO11
P104			SI11
P105			SCK11
P106	-		TIUD
P107			TCUD

(2) Non-port pins (1/2)

Pin	I/O	Function	Dual-function pin
RTP0	0	Outputs a pulse in real time as triggered by a trigger signal sent from the	P00/ADTRG0
RTP1		real-time pulse unit.	P01/ADTRG1
RTP2			P02/ADTRG2
RTP3			P03/ADTRG3
RTP4-RTP7			P04-P07
NMI	l	Nonmaskable interrupt request input	P20
INTPO		External interrupt request input	P21/TO04
INTP1			P22/TO05
INTP2			P23
INTP3			P24
INTP4			P25
TIO	1	External count clock input to timer 0	P81/TO03
TI1		External count clock input to timer 1	P36/TO11
TIUD		External count clock input to the up/down counter	P106
TCUD		Input for the control signal to determine whether the up/down counter counts up or down.	P107
TCLR0		Clear signal input to the real-time pulse unit	P80
TCLR1			P35
TCLR2			P26/TO21
TCLRUD			P85
TO00	0	Timer output from the real-time pulse unit (RPU)	P82
TO01			P83
TO02			P84
TO03			P81/TI0
TO04			P21/INTP0
TO05			P22/INTP1
TO10			P37
TO11			P36/T11
TO20			P27
TO21			P26/TCLR2
ANIO-ANI7		Analog input to the A/D converter	P70-P77
ADTRG0		External trigger signal input to the A/D converter	P00/RTP0
ADTRG1			P01/RTP1
ADTRG2			P02/RTP2
ADTRG3			P03/RTP3
ANO0	0	Analog output from the D/A converter	
ANO1			
TxD	0	Serial data output from the asynchronous serial interface	P30
RxD		Serial data input to the asynchronous serial interface	P31

(2) Non-port pins (2/2)

Pin	I/O	Function	Dual-function pin
SCK00	I/O	Serial clock I/O for the clock synchronous serial interface	P34
SCK10			P102
SCK11			P105
SI00	I	Serial data input to the clock synchronous serial interface in the 3-wire mode	P33/SB1
SI10			P101
SI11			P104
SO00	0	Serial data output from the clock synchronous serial interface in the 3-wire	P32/SB0
SO10		mode	P100
SO11			P103
SB0	1/0	Serial data I/O for the clock synchronous serial interface in the SBI mode	P32/SO00
SB1			P33/SI00
PWM0	0	PWM signal output	P86
PWM1			P87
WDTO	0	Output for the signal which indicates the watchdog timer overflowed. (A nonmaskable interrupt is generated.)	
AD0-AD7	1/0	Lower-order bits of the multiplexed address/data bus used when external memory is expanded	P40-P47
AD8-AD15		Higher-order bits of the multiplexed address/data bus used when external memory is expanded	P50-P57
ASTB	0	Output for the timing signal used in externally latching address information output from the AD0 to AD15 pins, in order to access the external memory	_
RD		Read strobe signal output to the external memory	P90
LWR		Write strobe signal output to the 8 low-order bits in the external memory	P91
HWR		Write strobe signal output to the 8 high-order bits in the external memory	P92
WAIT	1	Input for the control signal which causes wait in the bus cycle	
MODE0	I	Input for the control signal which sets the operation mode. Normally, both	-
MODE1		MODE0 and MODE1 are directly connected to the Vss pin.	
CLKOUT	0	System clock output	
RESET		System reset input	-
X1		Crystal input pin for the system clock. A clock signal provided externally	
X2		is input to the X1 pin. The X2 pin is left open.	
AVREF1		A/D converter reference voltage input	
AVREF2		D/A converter reference voltage input	
AV _{REF3}			
AVDD		Analog power supply for the A/D converter	-
AVss		Ground for the A/D converter	
VDD		Positive power supply	
Vss	_	Ground	
NC		Not internally connected. Connect the NC pin to the Vss pin (can also be left open).	





1.2 PROM PROGRAMMING MODE (MODE0/VPP = H, MODE1 = L, P21 = L, RESET = L)

Pin	1/0	Function
MODE0/Vpp	1	PROM programming mode set/programming supply voltage
MODE1		
P21	I	PROM programming mode set
RESET		
A0-A16	1	Address bus
D0-D7	1/0	Data bus
PGM	1	Program input
CE	1	Enable PROM
OE	- 1	Read strobe to PROM
Vdd		Positive power supply
Vss		GND

Caution Connect the MODE0/VPP, MODE1, P21, and RESET pins directly to the VDD or Vss pin.

1.3 INPUT/OUTPUT CIRCUIT TYPE FOR EACH PIN AND HANDLING OF UNUSED PINS

Table 1-1 lists the input and output circuit type for each pin and how to handle it when it is not used. Fig. 1-1 shows the circuits.

Table 1-1 Input/Output Circuit Type for Each Pin and Recommended Connection Methods for Unused Pins (1/2)

Pin	I/O circuit type	Recommended connection method
P00/RTP0/ADTRG0-P03/RTP3/ADTRG3	8-A	Input state : Each pin is connected to the VDD or
P04/RTP4-P07/RTP7	5-A	Vss pin via a separate resistor.
P10-P17		Output state : Open
P20/NMI	2	Connected to the Vss pin.
P21/INTP0/TO04	8-A	Input state : Each pin is connected to the V_{DD} or
P22/INTP1/TO05		Vss pin via a separate resistor.
P23/INTP2		Output state : Open
P24/INTP3		
P25/INTP4		
P26/TCLR2/TO21		
P27/TO20		
P30/TxD	5-A	
P31/RxD		
P32/SO00/SB0	10-A	
P33/SI00/SB1		
P34/SCK00	8-A	_
P35/TCLR1		
P36/TI1/TO11		
P37/TO10	5-A	
P40/AD0-P47/AD7		
P50/AD8-P57/AD15		
P70/ANI0-P77/ANI7	9	Connected to the Vss pin.
P80/TCLR0	8-A	Input state : Each pin is connected to the Voo or
P81/TI0/TO03		Vss pin via a separate resistor.
P82/TO00	5-A	Output state : Open
P83/TO01		
P84/TO02		
P85/TCLRUD	8-A	
P86/PWM0	5-A	
P87/PWM1		
P90/RD		
P91/LWR		
P92/HWR		
P93		



Table 1-1 Input/Output Circuit of Type for Each Pin and Recommended Connection Methods for Unused Pins (2/2)

Pin	I/O circuit type	Recommended connection method
P100/SO10	5-A	Input state $:$ Each pin is connected to the V _{DD} or
P101/SI10	8-A	Vss pin via a separate resistor.
P102/SCK10		Output state : Open
P103/SO11	5-A	
P104/SI11	8-A	
P105/SCK11		
P106/TIUD		
P107/TCUD		
ANO0, ANO1	12	Open
CLKOUT	3	
ASTB	4	
WDTO	19	Connected to the Vss pin.
WAIT	1	Connected to the VDD pin.
MODE0, MODE1	1	-
RESET	2	
AVREF1-AVREF3, AVSS	_	Connected to the Vss pin.
AVod		Connected to the VDD pin.
NC		Connected to the Vss pin (or open).

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Fig. 1-1 Input/Output Circuits of Each Pin



μ**ΡD78P356**

2. DIFFERENCES BETWEEN THE μ PD78P356 AND μ PD78356

The μ PD78P356 is produced by replacing the internal mask ROM of the μ PD78356 with a 48K-byte PROM. Both have the same functions except some differences in ROM specifications, such as write and verify modes. Table 2-1 shows the differences.

Phase-out/Discontinued

In this manual, the functions specific to the μ PD78P356 are explained. For details of the other functions, refer to the μ PD78356 document.

Item Part number	μΡD7	/8P356	μPD78356
Internal program memory (Electrical write)	One-time PROM (Data can be written once)	EPROM (Data can be written multiple times)	Mask ROM
ECC circuit	Provided	Not provided	
PROM programming terminal	Provided	· · · · · · · · · · · · · · · · · · ·	Not provided
Setting of MODE0 and MODE1	 Normal operation mode MODE0, 1 = LL Programming mode MODE0, 1 = HL ROM-less mode (with an external 16-bit bus) MODE0, 1 = HH 		 Normal operation mode MODE0, 1 = LL ROM-less mode (with an external 8-bit bus) MODE0, 1 = HL (with an external 16-bit bus) MODE0, 1 = HH
Package	100-pin plastic QFP120-pin plastic QFP	120-pin ceramic WQFN	100-pin plastic QFP 120-pin plastic QFP
Electrical characteristics	They differ in supply current a	nd other factors.	
Others	Since they differ in circuit scale radiation.	e and mask layout, they differ i	n noise immunity and noise

Table 2-1 Differences between the μ PD78P356 and μ PD78356

- Cautions 1. The PROM and mask ROM products differ in noise immunity and noise radiation. Use not ES products but CS products (mask ROM products) to evaluate them thoroughly when considering the change from the PROM products to the mask ROM products during processes from preproduction to volume production.
 - 2. Connect the MODE0 and MODE1 pins directly to the VDD or Vss pin.

 μ PD78P356

3. PROM PROGRAMMING

The μ PD78P356 is provided with an electrically writable PROM of 48K × 8 bits for programming and a PROM of 12K × 6 bits for error correcting codes (ECCs).

Phase-out/Discontinued

The ECCs correct errors of the codes written in the programming PROM, improving the reliability of data stored in the PROM.

Fig. 3-1 shows the memory map in the programming mode.



Fig. 3-1 Memory Map in the Programming Mode

Note The six low-order bits are effective in the ECC PROM.

Before programming the PROM, input appropriate signals to the MODE0/VPP, MODE1, P21, and RESET pins to change the mode to the PROM programming mode.

Program the PROM in the same way as for the μ PD27C1001A.

To use the ECCs, reset the lowest-order bit (F000.0) in the lowest-order byte of ECW (ECC control word) to enable the ECC circuit operation. The ECW is a 4-byte register for controlling the ECC circuit operation.

The ECCs and ECW are automatically generated by ECCGEN (ECC generator) supplied with the RA78K3 assembler package. (The ECCs are generated in the six low-order bits of the PROM. The two high-order bits are fixed to 1.)

Function	Normal operation mode	Programming mode					
Address input	P00-P07, P50, P20, P51-P57	A0-A16					
Data input	P40-P47	D0-D7					
Program pulse	P12	PGM					
Chip enable	P10	CE					
Output enable	P11	ŌĒ					
Program voltage	MODE	MODE0/Vpp					
Mode voltage	MODE1, P	MODE1, P21, RESET					

3.1 OPERATION MODE

To enter the program write/verify mode, set each pin as follows: MODE0/VPP = H, MODE1 = L, P21 = L, $\overrightarrow{\text{RESET}}$ = L. In addition, any of the operation modes listed in Table 3-2 can be selected by setting the $\overrightarrow{\text{CE}}$, $\overrightarrow{\text{OE}}$, and $\overrightarrow{\text{PGM}}$ pins in this mode.

Set the $\mu\text{PD78P356}$ to the read mode in order to read the contents of PROM.

Handle unused pins according to the caution in PIN CONFIGURATION (2).

Mode	MODE1	P21	RESET	ĈĒ	ŌĒ	PGM	MODE0/Vpp	VDD	D0-D7		
Page data latch				Н	L.	Н			Data input		
Page program]					Н	н	L			High impedance
Byte program				L	н	L	12.5 V	+12.5 V +6.5 V	+6.5 V	Data input	
Program verify				L	L	Н	+12.3 V	+0.5 V	Data output		
Program inhibit	L	L	L	×	L	L			High impedance		
				×	н	н					
Read				L	L	н			Data output		
Output disable				L	н	×	+5 V	+5 V	+5 V +5 V High in		
Standby				н	×	×			High impedance		

Table 3-2 Operation Modes for PROM Programming

Remark L: Directly connected to the Vss pin

H: Directly connected to the Vop pin

 \times : L or H

3.2 PROCEDURE FOR WRITING ON PROM (PAGE PROGRAM MODE)

The following is a procedure for writing on PROM. (See Fig. 3-2.)

In the page program mode, data is written in units of pages (four bytes). When write data completes midway of a page, latch FFH after the data so that the data fits into pages.

- (1) Always set each pin as follows: MODE0/VPP = H, MODE1 = L, P21 = L, and RESET = L. Connect unused pins according to PIN CONFIGURATION (2).
- (2) Apply +6.5 V to the VDD pin and +12.5 V to the MODE0/VPP pin.
- (3) Input an initial address to the A0 to A16 pins.
- (4) Clear the page counter.
- (5) Data latch mode. Input write data to the D0 to D7 pins and input an active-low pulse to the \overline{OE} pin. Increment the address and the page counter.
- (6) Repeat step (5) for a page (four bytes).
- (7) Input a 0.1 ms program pulse (active low) to the PGM pin.
- (8) Verify mode. Checks if data has been written in PROM.

Apply a low level to the \overline{CE} pin, input an active-low pulse to the \overline{OE} pin, and then read the write data from the D0 to D7 pins. Repeat this for a page (four bytes). When verification completes, apply a high level to the \overline{CE} pin.

- If data has been written, go to step (10).
- If not, repeat steps (7) and (8). If no data is written yet after the steps have been repeated 10 times, go to step (9).
- (9) Assume the device to be defective and stop write operation.
- (10) Increment the address.
- (11) Repeat steps (4) to (10) until the address exceeds the last address.

Fig. 3-3 is a timing chart of these steps (2) to (9).

Fig. 3-2 Flowchart of Procedure for Writing (Page Program Mode)



Note If write data does not fill a page, latch FFH for the rest of the page.

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3.3 PROCEDURE FOR WRITING ON PROM (BYTE PROGRAM MODE)

The following is a procedure for writing on PROM. (See Fig. 3-4.)

- Always set each pin as follows: MODE0/VPP = H, MODE1 = L, P21 = L, and RESET = L. Connect unused pins (1) according to PIN CONFIGURATION (2).
- Apply +6.5 V to the VDD pin and +12.5 V to the MODE0/VPP pin, and input a low-level signal to the \overline{CE} pin. (2)
- Input an initial address to the A0 to A16 pins. (3)
- Input write data to the D0 to D7 pins. (4)
- Input a 0.1 ms program pulse (active low) to the PGM pin. (5)
- Verify mode. Checks if data has been written in PROM. (6)

Input an active-low pulse to the \overline{OE} pin and read the write data from the D0 to D7 pins.

- If data has been written, go to step (8).
- If not, repeat steps (4) to (6). If no data is written yet after the steps have been repeated 10 times, go to step (7).
- Assume the device to be defective and stop write operation. (7)
- (8) Increment the address.
- Repeat steps (4) to (8) until the address exceeds the last address. (9)

Fig. 3-5 is a timing chart of these steps (2) to (7).

Fig. 3-4 Flowchart of Procedure for Writing (Byte Program Mode)



Fig. 3-5 PROM Write/Verify Timing Chart (Byte Program Mode)



3.4 PROCEDURE FOR READING FROM PROM

The following is a procedure for reading out the contents of PROM to the external data bus (D0 to D7).

- (1) Always set each pin as follows: MODE0/VPP = H, MODE1 = L, P21 = L, and RESET = L. Connect unused pins according to PIN CONFIGURATION (2).
- (2) Apply +5 V to the Vob and MODE0/VPP pins.
- (3) Input the address of data to be read into the A0 to A16 pins.
- (4) Read mode ($\overline{CE} = L, \overline{OE} = L$)
- (5) Output the data on the D0 to D7 pins.

Fig. 3-6 is a timing chart of these steps (2) to (5).





4. ERASURE CHARACTERISTICS (µPD78P356KP-S ONLY)

Data written in the μ PD78P356KP-S program memory can be erased (FFH); therefore users can write other data in the memory.

To erase the written data, expose the erasure window to light with a wavelength shorter than approx. 400 nm. Normally, ultraviolet light with a wavelength of 254 nm is employed. The amount of light required to completely erase the data is as follows:

- Intensity of ultraviolet light × erasing time: 15 W•s/cm² min.
- Erasing time: 15 to 20 minutes (When using a 12,000 μW/cm² ultraviolet lamp. It may, however, take more time due to lamp deterioration, dirt on the erasure window, or the like.)

The ultraviolet lamp should be placed within 2.5 cm from the erasure window during erasure. In addition, if a filter is attached to the ultraviolet lamp, remove the filter before erasure.

5. PROTECTIVE FILM COVERING THE ERASURE WINDOW (µPD78P356KP-S ONLY)

After the erasure window of the μ PD78P356KP-S has been exposed to sunlight or a fluorescent lamp for a long time, data in EPROM may be erased and the internal circuits may malfunction. To prevent these failures, the erasure window should be covered with a protective film when it is not used for erasure.

EPROM package products with a window are supplied with a NEC-guaranteed protective film when they are delivered.

6. SCREENING ONE-TIME PROM PRODUCTS

NEC cannot execute a complete test of one-time PROM products (μ PD78P356GC-7EA, μ PD78P356GD-5BB) due to their structure before shipment. It is recommended that you screen (verify) PROM products after writing necessary data into them and storing them at 125 °C for 24 hours.

NEC offers a charged service called QTOP microcomputer service. This service includes writing to one-time PROM, marking, screening, and verification. For the μ PD78P356, this service is yet to be supported. Ask your sales representative for details.

7. ELECTRICAL CHARACTERISTICS

ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

Parameter	Symbol		Conditions	Rating	Unit
	VDD			-0.5 to +7.0	٧
	AVDD			-0.5 to V _{DD} + 0.5	V
Supply voltage	Vpp			-0.5 to +13.5	V
	AVss			0.5 to +0.5	V
Input voltage	Vi		Note 1	-0.5 to V _{DD} + 0.5	V
Output voltage	Vo			-0.5 to V _{DD} + 0.5	V
Low-level output current		Each pin		pin 4.0	
	loL	Total of all output pins		140	mA
		Each pin		1.0	mA
High-level output current	Іон	Total of all output pins		-30	mA
Analog input voltage	Vian	Note 2	AVDD > VDD	-0.5 to Vpp + 0.5	V
			V _{DD} ≥ AV _{DD}	-0.5 to AV _{DD} + 0.5	
A/D converter reference input voltage	AVREF		AVDD > VDD	-0.5 to VDD + 0.5	V
			Vdd ≥ AVdd	0.5 to AV _{DD} + 0.5	
Operating temperature	TA			10 to +70	°C
Storage temperature	Tstg	· ·		-65 to +150	°C

Notes 1. Pins other than those listed below

- 2. P70/ANI0 P77/ANI7
- Caution Absolute maximum ratings are rated values beyond which some physical damages may be caused to the product; if any of the parameters in the table above exceeds its rated value even for a moment, the quality of the product may deteriorate. Be sure to use the product within the rated values.

RECOMMENDED OPERATING CONDITIONS

Oscillator frequency	ΤΑ	Vod
8 MHz ≤ fxx ≤ 32 MHz	10 to +70 °C	+5.0 V ±10 %

CAPACITANCE (TA = 25 °C, Vss = VDD = 0 V)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input capacitance	Cı				20	рF
Output capacitance	Co	f = 1 MHz			20	рF
I/O capacitance	Cio	0 V on pins other than measured pins			20	рF



OSCILLATOR CHARACTERISTICS (TA = -10 to +70 °C, VDD = +5 V \pm 10 %, Vss = 0 V)

Resonator	Recommended circuit	Parameter	Min.	Max.	Unit
Ceramic resonator or crystal	$V_{SS} X1 X2$ $\downarrow \downarrow $	Oscillator frequency (fxx)	8	32	MHz
External clock		X1 input frequency (fx)	8	32	MHz
	X1 X2 Open	X1 input rising and falling times (txn, txr)	0	10	ns
	HCMOS inverter	X1 input high-level and low- level widths (twxH, twxL)	10	115	ns

Caution When using the system clock generator, run wires in the portion surrounded by dotted lines according to the following rules to avoid effects such as stray capacitance:

- Minimize the wiring.
- Never cause the wires to cross other signal lines or run near a line carrying a large varying current.
- Cause the grounding point of the capacitor of the oscillator circuit to have the same potential as Vss. Never connect the capacitor to a ground pattern carrying a large current.
- Never extract a signal from the oscillator.

DC CHARACTERISTICS (TA = -10 to +70 °C, VDD = +5 V \pm 10 %, Vss = 0 V)

Parameter	Symbol	Conditions		Min.	Тур.	Max.	Unit
Low-level input voltage	VIL			0		0.8	V
High-level input voltage	Инт		Note 1	2.2			v
	ViH2		Note 2	0.8Vdd	- <u>.</u>		
Low-level output voltage	Vol	lo∟ = 2.0 mA	lo∟ = 2.0 mA			0.45	v
High-level output voltage	Vон	Іон = -400 <i>µ</i> А	\	Vdd - 1.0			V
Input leakage current	lu	Note 3	$0 V \leq V_{I} \leq V_{DD}$			±10	μA
		MODE0/Vpp	VI = VDD			+10	μA
	pin	Vi = 0 V			-200	μA	
Analog pin input leakage current	ILIAN	Note 4	$0 V \leq V_{I} \leq AV_{REF}$			±10	μA
Output leakage current	Ilo	$0 V \le V_0 \le V_0$	DD			±10	μA
Vpp supply current	loot	Operation mo	de		86	125	mA
	1002	HALT mode	HALT mode		40	60	mA
Data retention voltage	VDDDR	STOP mode		2.5			V
Data retention current	IDDDR	0700	VDDDR = 2.5 V		2	20	μA
		STOP mode	$V_{DDDR} = 5.0 \text{ V} \pm 10 \%$		10	50	μA
Software pull-up resistance	RL	V1 = 0 V		20	40	90	kΩ

Notes 1. For pins other than those described in Note 2

- RESET, X1, X2, P00/RTP0/ADTRG0, P01/RTP1/ADTRG1, P02/RTP2/ADTRG2, P03/RTP3/ADTRG3, P20/NMI, P21/INTP0/TO04, P22/INTP1/TO05, P23/INTP2, P24/INTP3, P25/INTP4, P26/TCLR2/TO21, P27/TO20, P32/SO00/SB0, P33/SI00/SB1, P34/SCK00, P35/TCLR1, P36/TI1/TO11, P80/TCLR0, P81/TI0/TO03, P85/TCLRUD, P101/SI10, P102/SCK10, P104/SI11, P105/SCK11, P106/TIUD, and P107/TCUD
- 3. For input and input/output pins (excluding MODE0/VPP, X1, X2, and P70/ANI0 to P77/ANI7 being used for analog input.)
- 4. For P70/ANI0 to P77/ANI7 (only when being used for analog input, during nonsampling operation)

AC CHARACTERISTICS (TA = -10 to +70 °C, VDD = +5 V \pm 10 %, Vss = 0 V, CL = 100 pF, fxx = 32 MHz)

Read/Write Operation (When the General Memory Is Connected)

Parameter	Symbol	Conditions	Min.	Max.	Unit
System clock cycle time	tсук		62.5	250	ns
Address setup time (to ASTB \downarrow)	İ SAST		7		ns
Address hold time (to ASTB \downarrow)	t HSTA		11		ns
Delay from $\overline{RD}\downarrow$ to address float	t fra			0	ns
Delay from address to data input	t daid			100	ns
Delay from $\overline{RD}\downarrow$ to data input	torid			49	ns
Delay from ASTB \downarrow to \overline{RD} \downarrow	t dstr		15		ns
Data hold time (to \overline{RD} \uparrow)	thrid		0		ns
Delay from RD ↑ to address active	Î DRA		17		ns
RD low-level width	twr⊾		63		ns
ASTB high-level width	twsтн		14		ns
Delay from \overline{LWR} , $\overline{HWR}\downarrow$ to data output	towop			21	ns
Delay from ASTB \downarrow to LWR, HWR \downarrow	tdstw		15		ns
Delay from LWR, HWR ↑ to ASTB ↑	towst		78		ns
Data setup time (to LWR, HWR ↑)	tsopw		57		ns
Data hold time (to \overline{LWR} , \overline{HWR} \uparrow)	tнwop		8		ns
LWR, HWR low-level width	tww.		63		ns
WAIT setup time (to address)	t sawt			47	ns
WAIT hold time (to address)	tнаwт		93		ns
WAIT setup time (to ASTB ↓)	tsasry			15	ns
\overline{WAIT} hold time (to ASTB \downarrow)	thashy		62		ns
$\overline{\text{WAIT}}$ setup time (to $\overline{\text{RD}}\downarrow$)	İSRRY			25	ns
$\overline{\text{WAIT}}$ setup time (to $\overline{\text{LWR}}$, $\overline{\text{HWR}} \downarrow$)	tsway			-25	ns
WAIT hold time (to $\overline{RD} \downarrow$)	tняяv		22		ns
\overline{WAIT} hold time (to \overline{LWR} , $\overline{HWR}\downarrow$)	thway		22		ns
Delay from address to $\overline{RD}\downarrow$	tdar .			77	ns
Delay from address to \overline{LWR} , $\overline{HWR}\downarrow$	tdaw			77	ns
Delay from WAIT ↑ to data input	τοωτιο			52	ns
Delay from WAIT ↑ to RD ↑	towtr		62		ns
Delay from WAIT ↑ to LWR, HWR ↑	towtw		62		ns

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tcyk-Dependent Bus Timing Definition

Symbol	Formula	Min./Max.	Unit
İ SAST	(0.5 + a)T – 24	Min.	ns
thsta	0.5T – 20	Min.	ns
twsтн	(0.5 + a)T – 17	Min.	ns
t dstr	0.5T - 16	Min.	ns
twal	(1.5 + n)T - 30	Min.	ns
t daid	(2.5 + a + n)T - 56	Max.	ns
ίdrid	(1.5 + n)T - 44	Max.	ns
t dra	0.5T – 14	Min.	ns
tostw	0.5T – 16	Min.	ns
t owst	1.5T 15	Min.	ns
twwL	(1.5 + n)T - 30	Min.	ns
ΐρωορ	0.5T - 10	Max.	ns
tsodw	(1 + n)T - 5	Min.	ns
tsawt	(a + n)T - 15	Max.	ns
thawt	(0.5 + a + n)T	Min.	ns
t sasry	(n – 0.5)T – 16	Max.	ns
thasry	nT	Min.	ns
İ SRRY	(n – 1)T – 25	Max.	ns
İ SWRY	(n – 1)T – 25	Max.	ns
ÎHRRY	(n – 0.5)T – 9	Min.	ns
thway	(n – 0.5)T – 9	Min.	ns
t dar	(a + 1)T + 15	Max.	ns
tdaw	(a + 1)T + 15	Max.	ns
ίρωτιο	T - 10	Max.	ns
towtr	Т	Min.	ns
t owtw	Т	Min.	ns

Phase-out/Discontinued

Remarks 1. T = tcyk = 1/fclk (fclk is the internal system clock frequency.)

- 2. When an address wait is inserted, the value of a is 1. Otherwise, it is 0.
- 3. The number n represents the number of wait cycles specified by the external wait pin (WAIT) or PWC register.
- 4. Only the bus timing items listed above are dependent on tcyk.

Serial Operation (T_A = -10 to +70 °C, V_{DD} = +5 V ±10 %, Vss = 0 V)

Parameter	Symbol		Min.	Max.	Unit	
O stal shark souls that		SCK output	Internal, divided by 8	500		ns
Serial clock cycle time	tcysk	SCK input	External clock	500		ns
Serial clock low-level width		SCK output	Internal, divided by 8	210		ns
	twskl	SCK input	External clock	210		ns
		SCK output	Internal, divided by 8	210		ns
Serial clock high-level width	twsкн	SCK input	External clock	210		ns
SI setup time (to SCK ↑)	tsrxsk			80		ns
SI hold time (to \overline{SCK} \uparrow)	tнякях			80		ns
$\overline{SCK} \downarrow \to SO$ delay time	tdsktx	R = 1 kΩ, C =	100 pF		110	ns

tсук-Dependent Serial Operations

Symbol	Conditions		Formula	Min./Max.	Unit	
tсүзк	SCK output	Internal, divided by 8	8Т	Min.	ns	
	SCK input	External clock	8T	Min.	ns	
twsĸ∟	SCK output	Internal, divided by 8	4T – 40	Min.	ns	
	SCK input	External clock	4T – 40	Min.	ns	
twsкн	SCK output	Internal, divided by 8	4T – 40	Min.	ns	
	SCK input	External clock	4T – 40	Min.	ns	

Remarks 1. T = tcyk = 1/fcLk (fcLk is the internal system clock frequency.)

2. The items listed above are dependent on tcyk.

Up/Down Counter Operations (TA = -10 to +70 °C, VDD = +5 V \pm 10 %, Vss = 0 V)

Parameter	Symbol	Conditions		Min.	Max.	Unit
TIUD high/low level width	twriuh, twriul	Other than mode 4	NIUD = 0	250		ns
			NIUD = 1	1		μs
		Mode 4	NIUD = 0	500		ns
			NIUD = 1	1		μs
TCUD high/low level width	twrcuн, twrcul	Other than mode 4	NCUD = 0	250		ns
			NCUD = 1	1		μs
		Mode 4	NCUD = 0	500		ns
			NCUD = 1	1		μs
	twoluh, twolul		NRUD = 0	250		ns
TCLRUD high/low level width			NRUD = 1	1		μs
TCUD setup time (to TIUD ↑)	tstcu	Mode 3		0		ns
TCUD hold time (to TIUD 1)	tнтcu	Mode 3		125		ns
TIUD setup time (to TCUD)	ts4TIU	Mode 4		250		ns
TIUD hold time (to TCUD)	thatiu	Mode 4		250		ns
Cycle time for TIUD and TCUD	tcyc4	Mode 4		1		μs

Remark NIUD, NCUD, NRUD: Bits 5, 6, and 7 of the noise protection control register (NPC)

tcvk-Dependent Up/Down Counter Operations

Symbol	Conditions		Formula	Min./Max.	Unit
twtiuh, twtiul		NIUD = 0	4T		ns
	Other than mode 4	NIUD = 1	16T		
		NIUD = 0	8T	Min.	
	Mode 4	NIUD = 1	16T		
twtcuн, twtcul	Other than mode 4	NCUD = 0	4T		ns
		NCUD = 1	16T		
	Mode 4	NCUD = 0	8T	Min.	
		NCUD = 1	16T		
twrcluh, twrclul		NRUD = 0	4T		
		NRUD = 1	16T	Min.	ns
tнтси	Mode 3		2T	Min.	ns
ts4TIU	Mode 4		4T	Min.	ns
th4TIU	Mode 4		4T	Min.	ns

Remarks 1. T = toyk = 1/folk (folk is the internal system clock frequency.)

- 2. The items listed above are dependent on tcyk.
- 3. NIUD, NCUD, NRUD: Bits 5, 6, and 7 of the noise protection control register (NPC)

Other Operations (T_A = -10 to +70 °C, V_{DD} = +5 V ±10 %, Vss = 0 V)

Parameter	Symbol	Conditions	Min.	Max.	Unit
NMI high/low level width	twnih, twnil	No analog noise	2		μs
INTP0 high/low level width	twioн, twio∟		250		ns
INTP1 high/low level width	twith, twit		250		ns
INTP2 high/low level width	twizh, twizl		250		ns
INTP3 high/low level width	twiзн, twiз∟		250		ns
INTP4 high/low level width	twi4H, twi4L		250		ns
TIO high/low level width	twtion, twtiol	NI0 = 0	250		ns
		NIO = 1	1		μs
	twrnn, twrn∟	NI1 = 0	250		ns
TI1 high/low level width		NI1 = 1	1		μs
	twoloh, twolol	NR0 = 0	250		ns
TCLR0 high/low level width		NR0 = 1	1		μs
		NR1 = 0	250		ns
TCLR1 high/low level width	twolih, twolil	NR1 = 1	1		μs
	twolzh, twolzl	NR2 = 0	250	· · · · · · · · · · · · · · · · · · ·	ns
TCLR2 high/low level width		NR2 = 1	1		μs
RESET high/low level width	twrsh, twrsl	No analog noise	1.5		μs

Remark NI0, NI1 : Bits 0 and 2 of the noise protection control register (NPC) NR0, NR1, NR2: Bits 1, 3, and 4 of the noise protection control register (NPC)
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Other tcyk-Dependent Operations

Symbol	Conditions	Formula	Min./Max.	Unit
twion, twiol		4T	Min.	ns
twnн, twn∟		4T	Min.	ns
twi≥H, twi≥L		4T	Min.	ns
twiзн, twiз∟		4T	Min.	ns
twi4H, twi4L		4T	Min.	ns
	NI0 = 0	4T	- Min.	
twrioh, twriol	NI0 = 1	16T		ns
	NI1 = 0	4T .	Min.	
twrme, twrme	NI1 = 1	16T		ns
	NR0 = 0	4T		
twoloh, twolol	NR0 = 1	16T	Min.	ns
	NR1 = 0	4T		
twolih, twolil	NR1 = 1	16T	Min.	ns
	NR2 = 0	4T		
twoleh, twolel	NR2 = 1	16T	Min.	ns

Phase-out/Discontinued

Remarks 1. T = tcyk = 1/fclk (fclk is the internal system clock frequency.)

- 2. The bus timing items listed above are dependent on tcyk.
- **3.** NI0, NI1 : Bits 0 and 2 of the noise protection control register (NPC) NR0, NR1, NR2 : Bits 1, 3, and 4 of the noise protection control register (NPC)

AC Timing Test Points



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A/D CONVERTER CHARACTERISTICS (TA = -10 to +70 °C, AVDD = VDD = +5 V ±10 %, AVss = Vss = 0 V)

Phase-out/Discontinued

Parameter	Symbol		Conditions	Min.	Тур.	Max.	Unit
Resolution				10			bit
Total error ^{Note} 1		4.5 V ≤	$AV_{REF1} \leq AV_{DD}$			±0.4	%FSR
		3.4 V ≤	$AV_{REF1} \leq AV_{DD}$			±0.7	%FSR
Quantization error						±1/2	LSB
		A/D trig	ger mode	2			μs
Conversion time	tconv	Timer trigger mode, external trigger mode		2 + 5T			μs
Sampling time	t samp	tсук = 63	2.5 ns	7.5			tсүк
Zero-scale calibration Note 1		4.5 V ≤	$AV_{REF1} \leq AV_{DD}$		±1.5	±2.5	LSB
Zero-scale calibration to the		$3.4 \text{ V} \leq \text{AV}_{\text{REF1}} \leq \text{AV}_{\text{DD}}$			±1.5	±4.5	LSB
Full scale calibration ^{Note 1}		$4.5 \text{ V} \leq \text{AV}_{\text{REF1}} \leq \text{AV}_{\text{DD}}$			±1.5	±3.0	LSB
Full scale calibration. The f		$3.4 \text{ V} \leq \text{AV}_{\text{REF1}} \leq \text{AV}_{\text{DD}}$			±1.5	±4.5	LSB
Neeliseerik, selikuskiseNote 1		4.5 V ≤	AVREF1 ≤ AVDD		±1.5	±2.5	LSB
Nonlinearity calibration ^{Note 1}		$3.4 \text{ V} \leq \text{AV}_{\text{REF1}} \leq \text{AV}_{\text{DD}}$			±1.5	±4.5	LSB
Analog input voltage ^{Note 2}	Vian			-0.3		AVREF1 + 0.3	V
A I		Nonsampling			10		MΩ
Analog input impedance	Ran	Sampling			Note 3		
Reference voltage	AVREF1			3.4		AVDD	V
AVREF1 current	Alrefi				3.0	8.0	mA
AV _{DD} supply current	Aldd	Operation mode			3.3	13.0	mA
A/D converter data retention		STOP	AVDDDR = 2.5 V		2	10	μA
current	Aldddr	mode AV _{DDDR} = 5 V ±10 %			10	50	μA

Notes 1. Quantization error is excluded.

 When -0.3 V ≤ VIAN ≤ 0 V, the conversion result is 000H. When 0 V < VIAN < AVREF1, the voltage is converted with a 10-bit resolution. When AVREF1 ≤ VIAN ≤ AVREF1 + 0.3 V, the conversion result is 3FFH.

3. During sampling, the analog input impedance is equal to that of the following equivalent circuit. (The figure below shows typical values. These values may not be correct for your application.)



Remark $T = t_{CYK} = 1/f_{CLK}$ (f_CLK is the internal system clock frequency.)



D/A CONVERTER CHARACTERISTICS (TA = -10 to +70 °C, AVREF2 = VDD = +5 V ±10 %, AVREF3 = VSS = 0 V)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Resolution					8	bit
Total error		$AV_{REF2} = V_{DD} = +5 V,$ $AV_{REF3} = V_{SS} = 0 V$			±0.4	%
Setting time		Load: 2 MΩ, 30 pF			2	μs
Output resistance	R∘	DACS0, DACS1 = 7FH		10		kΩ
Analog reference voltage	AV _{REF2}		0.75Vdd		VDD	V
Analog reference voltage	A Vref3		Vss		0.2Vdd	V
Reference power supply input current	Alref2		0		5	mA
Reference power supply input current	Alref3		-5		0	mA

Read Operation (for 8-bit)





Read Operation (for 16-bit)

NEC



μ**PD78P356**

Phase-out/Discontinued

Write Operation (for 16-bit)

NEC



Serial Operation









Interrupt Input Timing



Remark n = 0 to 4









Remark n = 0 or 1





DC PROGRAMMING CHARACTERISTICS (TA = 25 ± 5 °C, Vss = 0 V)

Parameter	Symbol	Symbol ^{Note 1}	Conditions	Min.	Тур.	Max.	Unit
High-level input voltage	Vін	Vih		2.2		Vddp + 0.3	V
Low-level input voltage	VIL	Vı∟		-0.3		0.8	V
Input leakage current	LIP	lu	$0 \le V_1 \le V_{DDP}$ Note 2			±10	μA
High-level output voltage	Vон	Vон	I _{OH} = -400 μA	2.4			V
Low-level output voltage	Vol	Vol	lo _L = 2.1 mA			0.45	V
Input current	la9	-	A9 (P20/NMI) pin			±10	μA
Output leakage current	llo	-	$0 \le V_0 \le V_{DDP}, \ \overline{OE} = V_{IH}$			±10	μA
VDDP supply voltage	VDDP	Vcc	Program memory write mode	6.25	6.5	6.75	V
			Program memory read mode	4.5	5.0	5.5	V
VPP supply voltage	Vpp	Vpp	Program memory write mode	12.2	12.5	12.8	V
			Program memory read mode	VPP = VDDP		I I DDP	V
VDDP supply current	σαΙ	laa	Program memory write mode	**************************************		30	mA
			Program memory read mode			100	mA
VPP supply current	IPP	Ірр	Program memory write mode			50	mA
			Program memory read mode		1.0	100	μA

Notes 1. Symbols for the corresponding μ PD27C1001A

2. The VDDP represents the VDD pin as viewed in the programming mode.

AC PROGRAMMING CHARACTERISTICS (TA = 25 ±5 °C, Vss = 0 V)

PROM Write Mode (Page Program Mode)

Parameter	Symbol ^{Note 1}	Conditions	Min.	Тур.	Max.	Unit
Address set up time	tas		2			μs
CE set time	tces		2			μs
Input data setup time	tos		2		1	μs
Address hold time	tан		2			μs
	tah∟		2			μs
	tahv		0			μs
Input data hold time	tон		2			μs
Output data hold time	tor		0		250	ns
VPP setup time	tvps		2			μs
VDDP setup time	tvDsNote 2		2			μs
Initial program pulse width	tew		0.095	0.1	0.105	ms
OE set time	toes		2			μs
Valid data delay time from OE	toe				1.0	μs
OE pulse width in the data latch	tLw		1			μs
PGM setup time	tрgms		2			μs
CE hold time	tсен		2			μs
OE hold time	tоен		2			μs

Notes 1. These symbols (except tvos) correspond to those of the μ PD27C1001A.

2. For μ PD27C1001A, read tvps as tvcs.

PROM Write Mode (Byte Program Mode)

Parameter	Symbol ^{Note 1}	Conditions	Min.	Тур.	Max.	Unit
Address set up time	tas		2			μs
CE set time	tces		2			μs
Input data setup time	tos		2			μs
Address hold time	tан		2			μs
Input data hold time	tон		2			μs
Output data hold time	tor		0		250	ns
VPP setup time	tvps		2			μs
VDDP setup time	tvosNote 2		2			μs
Initial program pulse width	tew		0.095	0.1	0.105	ms
OE set time	toes		2			μs
Valid data delay time from \overline{OE}	toe				1.0	μs

Notes 1. These symbols (except tvos) correspond to those of the μ PD27C1001A.

2. For μ PD27C1001A, read tvps as tvcs.

PROM Read Mode

Parameter	Symbol ^{Note}	Conditions	Min.	Тур.	Max.	Unit
Data output time from address	tacc	$\overline{CE} = \overline{OE} = V_{IL}$			1.0	μs
$\overline{CE}\downarrow\todata$ output time	tce	OE = VIL			1.0	μs
$\overline{OE} \downarrow \rightarrow data$ output time	toe	CE = VIL			1.0	μs
Data hold time to $\overline{OE} \uparrow$	tor	CE = VIL	0		250	ns
Data hold time to address	tон	$\overline{CE} = \overline{OE} = V_{IL}$	0			ns

Note These symbols correspond to those of the μ PD27C1001A.



PROM Write Mode Timing (Page Program Mode)



NEC

Phase-out/Discontinued PROM Write Mode Timing (Byte Program Mode)



Cautions 1. VDDP must be applied before VPP, and must be cut after VPP.

- 2. VPP including overshoot must not exceed +13.5 V.
- 3. Plugging in or out the board with the VPP pin supplied with 12.5 V may adversely affect its reliability.

PROM Read Mode Timing



Notes 1. For reading within tacc, the delay of the OE input from falling edge of CE must be within tacc - toe. 2. tor is the time measured from when either \overline{OE} or \overline{CE} reaches VIH, whichever is faster.

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NEC





Phase-out/Discontinued





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μ**PD78P356**

Phase-out/Discontinued









NEC





9. PACKAGE DRAWINGS

100 PIN PLASTIC QFP (FINE PITCH) (14)





Each lead centerline is located within 0.10 mm (0.004 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
A	16.0±0.2	0.630±0.008
В	14.0±0.2	0.551+0.009 -0.008
С	14.0±0.2	0.551+0.009
D	16.0±0.2	0.630±0.008
F	1.0	0.039
G	1.0	0.039
н	$0.22^{+0.05}_{-0.04}$	0.009±0.002
	0.10	0.004
J	0.5 (T.P.)	0.020 (T.P.)
к	1.0±0.2	$0.039^{+0.009}_{-0.008}$
L	0.5±0.2	0.020+0.008
М	0.17+0.03	0.007+0.001 -0.003
N	0.10	0.004
Р	1.45	0.057
Q	0.125±0.075	0.005±0.003
R	5°±5°	5°±5°
S	1.7 MAX.	0.067 MAX.
		P100GC-50-7EA-2

μ**PD78P356**

120-pin plastic QFP (28 x 28) (units: mm)



Phase-out/Discontinued

P120GD-80-5BB-3

120 PIN CERAMIC WOFN



NOTE

Each lead centerline is located within 0.08 mm (0.003 inch) of its true position (T.P.) at maximum material condition.

		X120KW-80A-1
ITEM	MILLIMETERS	INCHES
A	27.3±0.27	1.075±0.011
В	24.5	0.965
С	24.5	0.965
D	27.3±0.27	1.075±0.011
E	1.94	0.076
F	2.14	0.084
G	3.57 MAX.	0.141 MAX.
н	0.51±0.10	0.020±0.004
	0.08	0.003
J	0.8	0.031
к	1.0±0.15	0.039+0.007
Q	C0.3	C0.012
R	2.05	0.081
S	2.05	0.081
Т	R3.0	R0.118
U	12.0	0.472
U1	1.5	0.059
U2	1.0	0.039
Y	C1.0	C0.039
Z	0.10	0.004



10. RECOMMENDED SOLDERING CONDITIONS

The conditions listed below shall be met when soldering the μ PD78P356.

For details of the recommended soldering conditions, refer to our document *SMD Surface Mount Technology Manual* (IEI-1207).

Phase-out/Discontinued

Please consult with our sales offices in case any other soldering process is used, or in case soldering is done under different conditions.

Table 10-1 Soldering Conditions for Surface-Mount Devices (1)

μ PD78P356GC-7EA: 100-pin plastic QFP (14 \times 14 mm)

Soldering process	Soldering conditions	Symbol
Infrared ray reflow	 Peak package's surface temperature: 235 °C Reflow time: 30 seconds or less (at 210 °C or more) Maximum allowable number of reflow processes: 2 Exposure limit^{Note}: 7 days (10 hours of pre-baking is required at 125 °C afterward.) <cautions> (1) Do not start reflow-soldering the device if its temperature is higher than the room temperature because of a previous reflow soldering. (2) Do not use water for flux cleaning before a second reflow soldering. </cautions> 	IR35-107-2
VPS	 Peak package's surface temperature: 215 °C Reflow time: 40 seconds or less (at 200 °C or more) Maximum allowable number of reflow processes: 2 Exposure limit^{Note}: 7 days (10 hours of pre-baking is required at 125 °C afterward.) <cautions> (1) Do not start reflow-soldering the device if its temperature is higher than the room temperature because of a previous reflow soldering. (2) Do not use water for flux cleaning before a second reflow soldering. </cautions> 	VP15-107-2
Wave soldering	Solder temperature: 260 °C or less Flow time: 10 seconds or less Number of flow process: 1 Preheating temperature: 120 °C max. (measured on the package surface) Exposure limit ^{Note} : 7 days (10 hours of pre-baking is required at 125 °C afterward.)	WS60-107-1
Partial heating method	Terminal temperature: 300 °C or less Flow time: 3 seconds or less (for each side of device)	-

Note Exposure limit before soldering after dry-pack package is opened.

Storage conditions: Temperature of 25 °C and maximum relative humidity at 65 % or less

Caution Do not apply more than a single process at once, except for "Partial heating method."



Table 10-2 Soldering Conditions for Surface-Mount Devices (2)

μ PD78P356GD-5BB: 120-pin plastic QFP (28 \times 28 mm)

Soldering process	Soldering conditions	Symbol
Infrared ray reflow	 Peak package's surface temperature: 235 °C Reflow time: 30 seconds or less (at 210 °C or more) Maximum allowable number of reflow processes: 2 Exposure limit^{Note}: 7 days (36 hours of pre-baking is required at 125 °C afterward.) <cautions> (1) Do not start reflow-soldering the device if its temperature is higher than the room temperature because of a previous reflow soldering. (2) Do not use water for flux cleaning before a second reflow soldering. </cautions> 	IR35-367-2
VPS	 Peak package's surface temperature: 215 °C Reflow time: 40 seconds or less (at 200 °C or more) Maximum allowable number of reflow processes: 2 Exposure limit^{Note}: 7 days (36 hours of pre-baking is required at 125 °C afterward.) <cautions> (1) Do not start reflow-soldering the device if its temperature is higher than the room temperature because of a previous reflow soldering. (2) Do not use water for flux cleaning before a second reflow soldering. </cautions> 	VP15-367-2
Wave soldering	Solder temperature: 260 °C or less Flow time: 10 seconds or less Number of flow process: 1 Preheating temperature: 120 °C max. (measured on the package surface) Exposure limit ^{Note} : 7 days (36 hours of pre-baking is required at 125 °C afterward.)	WS60-367-1
Partial heating method	Terminal temperature: 300 °C or less Flow time: 3 seconds or less (for each side of device)	_

Note Exposure limit before soldering after dry-pack package is opened. Storage conditions: Temperature of 25 °C and maximum relative humidity at 65 % or less

Caution Do not apply more than a single process at once, except for "Partial heating method."

*

APPENDIX A TOOLS

A.1 DEVELOPMENT TOOLS

The following tools are provided for developing a system that uses the μ PD78P356:

Language processor

78K/III series relocatable assembler (RA78K/III)	macro functions, i A structured-prog description of prog	This relocatable program can be used for all 78K/III series emulators. With its macro functions, it allows the user to improve program development efficiency. A structured-programming assembler is also provided, which enables explicit description of program control structures. This assembler could improve productivity in program production and maintenance.					
	Host machine	OS	Distribution media	- Part number			
	PC-9800 series	MS-DOSTM	3.5-inch 2HD	μS5A13RA78K3			
			5.25-inch 2HD	μS5A10RA78K3			
	IBM PC/AT TM or	PC DOSTM	3.5-inch 2HC	μS7B13RA78K3			
	compatibles		5.25-inch 2HC	μS7B10RA78K3			
	HP9000 series 700 TM	HP-UXTM	DAT	μS3P16RA78K3			
	SPARC station TM	SunOS TM	Cartridge tape	μS3K15RA78K3			
	NEWSTM	NEWS-OS™	(QIC-24)	μS3R15RA78K3			
78K/III series C compiler (CC78K/III)	This C compiler can be used for all 78K/III series emulators. The compiler converts programs written in C language into object codes executable on the microcomputer. When the compiler is used, the 78K/III series relocatable assembler package (RA78K/III) is needed.						
	Host machine		Distribution media	Part number			
	PC-9800 series	OS	3.5-inch 2HD	μS5A13CC78K3			
	FO-3000 series	MS-DOS	5.25-inch 2HD	μS5A10CC78K3			
	IBM PC/AT or	PC DOS	3.5-inch 2HC	μS7B13CC78K3			
	compatibles	PC DOS	5.25-inch 2HC	μS7B10CC78K3			
	HP9000 series 700	HP-UX	DAT	μS3P16CC78K3			
	SPARCstation	SunOS	Cartridge tape	μS3K15CC78K3			
	NEWS	NEWS-OS	(QIC-24)	μS3R15CC78K3			

Remark It is guaranteed that the relocatable assembler and C compiler run only under the OSs on the corresponding host machines described above.





Connections between development tools and target devices

Development tool Target device		Emulation probe and EPROM product	Conversion adapter	Conversion socket or conversion adapter
GC package	IE-78350-R and	EP-78355GC-R		EV-9500GC-100
(100-pin QFP)	IE-78355-R-EM1	EP-78355GD-R	EV-9501GC-100	
		μΡD78Ρ356KP (120-pin WQFN)		
GD package (120-pin QFP)	IE-78350-R and IE-78355-R-EM1	EP-78355GD-R		EV-9200GD-120
		μΡD78Ρ356KP (120-pin WQFN)		

PROM programming tools

Hardware	PG-1500	optional program a puter containing Pl	The PG-1500 PROM programmer is used together with an accessory board and optional program adapter. It allows the user to program a single chip microcomputer containing PROM independently or from a host machine. The PG-1500 can be used to program typical 256K-bit to 4M-bit PROMs.			
	PA-78P356GC PA-78P356GD PA-78P356KP	PROM programme PA-78P356GC : PA-78P356GD :	Programmer adapter for writing programs to the μ PD78P356A. Used with a PROM programmer such as the PG-1500. PA-78P356GC : For μ PD78P356GC PA-78P356GD : For μ PD78P356GD PA-78P356KP : For μ PD78P356KP			
Software	PG-1500 controller	This program enab and parallel interfa		nine to control the PG-150	0 through the serial	
		Host machine	Host machine OS Distribution media		- Part number	
	PC	PC-9800 series	MS-DOS	3.5-inch 2HD	μS5A13PG1500	
				5.25-inch 2HD	μS5A10PG1500	
		IBM PC/AT or	PC DOS	3.5-inch 2HC	μS7B13PG1500	
		compatibles		5.25-inch 2HC	μS7B10PG1500	

Remark It is guaranteed that the PG-1500 controller runs only under the OSs on the corresponding host machines described above.

Debugging tools (when the IE controller is used)

Hardware	IE-78350-R	In-circuit emulator for developing and debugging an application system. For debugging, connect the emulator to the host machine.					
	IE-78355-R-EM1	I/O emulation board for emulating peripheral hardware such as the I/O ports of the target device.					
	EP-78355GC-R	Emulation probe for connecting the IE-78350-R to the target system, used for the 100- pin QFP of the μ PD78P356. The EV-9500GC-100 conversion adapter is supplied with					
	EV-9500GC-100	the emulation probe, to connect the target system.					
	EP-78355GD-R	Emulation probe for connecting the IE-78350-R to the target system, used for the 120-					
	EV-9200GD-120		pin QFP of the μ PD78P356. The EV-9200GD-120 conversion socket is supplied with the emulation probe, to connect the target system. By connecting this emulation probe to the optional 100-pin QFP conversion adapter, EV-9501GC-100, the 100-pin QFP of				
	EV-9501GC-100	to the optional 100-					
	+ EV-9500GC-100	the μ PD78356 can be developed. To connect the target system, however, also use the optional EV-9500GC-100 conversion adapter.			tem, however, also use the		
Software	IE-78350-R control program	1 0		o control the IE-78350-1 on ensures more efficie	R from the host machine. Its nt debugging.		
	(IE controller)				Destauration		
		Host machine	OS	Distribution media	Part number		
		PC-9800 series	MS-DOS	3.5-inch 2HD	μ\$5A13IE78355		
				5.25-inch 2HD	μS5A10IE78355		
		IBM PC/AT or	PC DOS	3.5-inch 2HC	μS7B13IE78355		
		compatibles		5.25-inch 2HC	μS7B10IE78355		

Phase-out/Discontinued

Remark It is guaranteed that the IE controller runs only under the OSs on the corresponding host machines described above.

Phase-out/Discontinued

Development tool configuration (when the IE controller is used)



Debugging tools (when the integrated debugger is used) (1/2)

Hardware IE-784000-R		00-R	In-circuit emulator for developing and debugging an application system. For debugging, connect the emulator to the host machine.	
	IE-78350-R-EM-ANote		Emulation board for emulating peripheral hardware such as the I/O ports of the target device.	
	IE-7835	5-R-EM1	I/O emulation board for emulating peripheral hardware such as the I/O ports of the target device.	
	EP-7835	55GC-R	Emulation probe for connecting the IE-784000-R to the target system, used for the 100-pin QFP of the μ PD78P356. One EV-9500GC-100 conversion adapter	
		EV-9500GC-100	is provided for connection to the target system.	
	EP-78355GD-R		Emulation probe for connecting the IE-784000-R to the target system, used for the 120-pin QFP of the μ PD78P356. The EV-9200GD-120 conversion socket is	
		EV-9200GD-120	supplied with the emulation probe, to connect the target system. By connecting this emulation probe to the optional 100-pin QFP conversion adapter, EV-	
		EV-9501GC-100	9501GC-100, the 100-pin QFP of the μ PD78356 can be developed. To conne	
		+ EV-9500GC-100	the target system, however, also use the optional EV-9500GC-100 conversion adapter.	
	IE-70000-98-IF-B IE-70000-98N-IF IE-70000-PC-IF-B		Interface adapter and cable when the PC-9800 series computer (other than a notebook) is used as the host machine.	
			Interface adapter and cable when a PC-9800 series notebook is used as the host machine.	
			Interface adapter and cable when the IBM PC/AT is used as the host machine.	
	IE-78000	D-R-SV3Note	Interface board when the EWS is used as the host machine.	

Phase-out/Discontinued

Note Under development

NEC

Phase-out/Discontinued

Debugging tools (when the integrated debugger is used) (2/2)

Software	Integrated debugger (ID78K/III)Note	Program for controlling the in-circuit emulator for the 78K/III series. The inte- grated debugger (ID78K/III) is used together with the device file (DF78355).			
		Debugging can be performed for the source program written in assembly language, or assembly language. The ID78K/III can information simultaneously on the host machine screen divided areas. This ensures efficient debugging.			display various
-		Host machine		1	Part number
			OS	Distribution media	. art nambor
		PC-9800 series	MS-DOS	3.5-inch 2HD	μSAA13ID78K3
			Windows TM	5.25-inch 2HD	μSAA10ID78K3
		IBM PC/AT or compatibles (Japanese Windows)	PC DOS	3.5-inch 2HC	μ SAB13ID78K3
			Windows	5.25-inch 2HC	μSAB10ID78K3
		IBM PC/AT or		3.5-inch 2HC	μSBB13ID78K3
		compatibles (Windows)		5.25-inch 2HC	μSBB10ID78K3
	Device file File which contains the device-specific infor (DF78355)Note used together with the assembler (RA78K/I grated debugger (ID78K/III).				
		Host machine	OS	Distribution media	Part number
		PC-9800 series	MS-DOS	3.5-inch 2HD	μS5A13DF78355
				5.25-inch 2HD	μS5A10DF78355
		IBM PC/AT or	PC DOS	3.5-inch 2HC	μS7B13DF78355
		compatibles		5.25-inch 2HC	μS7B10DF78355

Note Under development

Remark It is guaranteed that the integrated debugger and device file run only under the OSs on the corresponding host machines described above.

Development tool configuration (when the integrated debugger is used)



A.2 EMBEDDED SOFTWARE

To improve the efficiency of program development and simplify the maintenance of systems incorporating this microcomputer, the following embedded software is provided.

Phase-out/Discontinued

Real-time OS

Real-time OS (RX78K/III) ^{Note}	This operating system was designed to provide a multitasking environment for control applications that require real-time processing. System performance is improved by using the idling CPU for other processing. RX78K/III provides system calls that conform to μ ITRON specifications. The RX78K/III package provides the RX78K/III nucleus and a tool (Configurator) that is used for creating multiple information tables.			
	Host machine			Part number
		OS	Distribution media	
	PC-9800 series	MS-DOS	3.5-inch 2HD	Undecided
			5.25-inch 2HD	Undecided
	IBM PC/AT or	PC DOS	3.5-inch 2HC	Undecided
	compatibles		5.25-inch 2HC	Undecided

Note Under development

Caution Before purchasing this software, complete the purchase application sheet and sign the software license agreement.

Remark To use the RX78K/III real-time operating system, the optional RA78K/III assembler package is required.

Fuzzy inference development support system

Tool for creating fuzzy knowledge data	This program sup and membership		g and simulation of fuzzy kno	owledge data (fuzzy rules
(FE9000, FE9200)	Host machine			Part number
		OS NS DOS	3.5-inch 2HD	
	PC-9800 series	MS-DOS		μS5A13FE9000
			5.25-inch 2HD	μS5A10FE9000
	IBM PC/AT or compatibles	PC DOS + Windows	3.5-inch 2HC 5.25-inch 2HC	μS7B13FE9200 μS7B10FE9200
Translator (FT78K3) ^{Note}		•	l dge data, obtained using th burce program for RA78K/II	• •
	Host machine			Part number
		OS	Distribution media	
	PC-9800 series	MS-DOS	3.5-inch 2HD	μS5A13FT78K3
			5.25-inch 2HD	μS5A10FT78K3
	IBM PC/AT or	PC DOS	3.5-inch 2HC	μS7B13FT78K3
	compatibles		5.25-inch 2HC	μS7B10FT78K3
Fuzzy inference module (FI78K/III) ^{Note}			A construction of the second s	
-	This program pe Translator.	rforms fuzzy inferenc	e by linking the fuzzy know	ledge data converted by
-				Part number
•	Translator. Host machine	OS	Distribution media	Part number
•	Translator.		Distribution media 3.5-inch 2HD	Part number μS5A13FI78K3
•	Translator. Host machine PC-9800 series	OS	Distribution media 3.5-inch 2HD 5.25-inch 2HD	Part number μS5A13FI78K3 μS5A10FI78K3
•	Translator. Host machine PC-9800 series IBM PC/AT or	OS	Distribution media 3.5-inch 2HD	Part number μS5A13FI78K3
•	Translator. Host machine PC-9800 series	OS MS-DOS	Distribution media 3.5-inch 2HD 5.25-inch 2HD	Part number μS5A13FI78K3 μS5A10FI78K3
-	Translator. Host machine PC-9800 series IBM PC/AT or compatibles This software su	OS MS-DOS PC DOS	Distribution media 3.5-inch 2HD 5.25-inch 2HD 3.5-inch 2HC 5.25-inch 2HC 5.25-inch 2HC on and adjustment of fuzzy	Part number μS5A13FI78K3 μS5A10FI78K3 μS7B13FI78K3 μS7B10FI78K3
(FI78K/III) ^{Note} Fuzzy inference debugger	Translator. Host machine PC-9800 series IBM PC/AT or compatibles This software su hardware level, b	OS MS-DOS PC DOS	Distribution media 3.5-inch 2HD 5.25-inch 2HD 3.5-inch 2HC 5.25-inch 2HC 5.25-inch 2HC on and adjustment of fuzzy	Part number μS5A13FI78K3 μS5A10FI78K3 μS7B13FI78K3 μS7B10FI78K3
(FI78K/III) ^{Note} Fuzzy inference debugger	Translator. Host machine PC-9800 series IBM PC/AT or compatibles This software su hardware level, b Host machine	OS MS-DOS PC DOS upports the evaluation by using an in-circuit	Distribution media 3.5-inch 2HD 5.25-inch 2HD 3.5-inch 2HC 5.25-inch 2HC 5.25-inch 2HC on and adjustment of fuzzy	Part number μS5A13FI78K3 μS5A10FI78K3 μS7B13FI78K3 μS7B10FI78K3 knowledge data at the
(FI78K/III) ^{Note} Fuzzy inference debugger	Translator. Host machine PC-9800 series IBM PC/AT or compatibles This software su hardware level, b	OS MS-DOS PC DOS upports the evaluatio by using an in-circuit	Distribution media 3.5-inch 2HD 5.25-inch 2HD 3.5-inch 2HC 5.25-inch 2HC 5.25-inch 2HC on and adjustment of fuzzy emulator.	Part number μS5A13FI78K3 μS5A10FI78K3 μS7B13FI78K3 μS7B10FI78K3 knowledge data at the
(FI78K/III) ^{Note} Fuzzy inference debugger	Translator. Host machine PC-9800 series IBM PC/AT or compatibles This software su hardware level, b Host machine	OS MS-DOS PC DOS upports the evaluation by using an in-circuit	Distribution media 3.5-inch 2HD 5.25-inch 2HD 3.5-inch 2HC 5.25-inch 2HC 5.25-inch 2HC on and adjustment of fuzzy emulator. Distribution media	Part number µS5A13FI78K3 µS5A10FI78K3 µS7B13FI78K3 µS7B10FI78K3 r knowledge data at the Part number
(FI78K/III) ^{Note} Fuzzy inference debugger	Translator. Host machine PC-9800 series IBM PC/AT or compatibles This software su hardware level, b Host machine	OS MS-DOS PC DOS upports the evaluation by using an in-circuit	Distribution media 3.5-inch 2HD 5.25-inch 2HD 3.5-inch 2HC 5.25-inch 2HC 5.25-inch 2HC and adjustment of fuzzy emulator. Distribution media 3.5-inch 2HD	Part number µS5A13FI78K3 µS5A10FI78K3 µS7B13FI78K3 µS7B10FI78K3 knowledge data at the Part number µS5A13FD78K3

Phase-out/Discontinued

Note Under development

* APPENDIX B DRAWINGS OF THE CONVERSION ADAPTER

Fig. B-1 Drawings of the Conversion Adapter (EV-9500GC-100) (Reference)







EV-9500GC-100-G0

Fig. B-2 Drawings of the Conversion Adapter (EV-9501GC-100) (Reference)







EV-9501GC-100-G0



APPENDIX C DRAWINGS OF THE CONVERSION SOCKET AND RECOMMENDED PATTERN ON BOARDS

Caution Although the part number is EV-9200GD-120, number EV-9200G-120 is marked on the part.

Fig. C-1 Drawings of the Conversion Socket (EV-9200GD-120) (Reference)

Based on EV-9200G-120 (1) Package drawing (in mm)



		EV-9200G-120-G0
ITEM	MILLIMETERS	INCHES
A	32.3	1.272
В	27.6	1.087
С	27.6	1.087
D	32.3	1.272
E	4-C 3.0	4-C 0.118
F	0.8	0.031
G	11.0	0.433
н	29.3	1.154
1	32.0	1.26
J	11.0	0.433
к	29.3	1.154
L	32.0	1.26
М	8.0	0.315
N	7.8	0.307
0	2.5	0.098
Р	2.0	0.079
Q	0.35±0.1	0.014+0.004
R	¢2.3	¢0.091
S	ø1.5	¢0.059

μ**ΡD78Ρ356**



Phase-out/Discontinued



EV-9200G-120-P1

[MEMO]

Cautions on CMOS Devices

① Countermeasures against static electricity for all MOSs

Caution When handling MOS devices, take care so that they are not electrostatically charged. Strong static electricity may cause dielectric breakdown in gates. When transporting or storing MOS devices, use conductive trays, magazine cases, shock absorbers, or metal cases that NEC uses for packaging and shipping. Be sure to ground MOS devices during assembling. Do not allow MOS devices to stand on plastic plates or do not touch pins.

Also handle boards on which MOS devices are mounted in the same way.

(2) CMOS-specific handling of unused input pins

Caution Hold CMOS devices at a fixed input level.

Unlike bipolar or NMOS devices, if a CMOS device is operated with no input, an intermediatelevel input may be caused by noise. This allows current to flow in the CMOS device, resulting in a malfunction. Use a pull-up or pull-down resistor to hold a fixed input level. Since unused pins may function as output pins at unexpected times, each unused pin should be separately connected to the V_{DD} or GND pin through a resistor.

If handling of unused pins is documented, follow the instructions in the document.

③ Statuses of all MOS devices at initialization

Caution The initial status of a MOS device is unpredictable when power is turned on.

Since characteristics of a MOS device are determined by the amount of ions implanted in molecules, the initial status cannot be determined in the manufacture process. NEC has no responsibility for the output statuses of pins, input and output settings, and the contents of registers at power on. However, NEC assures operation after reset and items for mode setting if they are defined.

When you turn on a device having a reset function, be sure to reset the device first.

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License not needed : µPD78P356KP-S The customer must judge the need for license : µPD78P356GC-7EA and µPD78P356GD-5BB

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- Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
- Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
- Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices in "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact NEC Sales Representative in advance.

Anti-radioactive design is not implemented in this product.

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